



Road to Chiplets: Architecture

July 13 & 14, 2021



Chiplets: Building Blocks and Future Packaging Trends

Dave Hiner | Sr. Director
Advanced Package Technology Integration

Mike Kelly | VP
Advanced Package Technology Integration

Agenda

- 1 High Level Trends
- 2 What is a Chiplet?
- 3 Chiplet Motivation
- 4 Packaging Technologies for Chiplet-based Products



Market Driver and Trends

June 2021

High Performance Product and Packaging Trends

Higher memory BW
at low power

- ▶ Memory co-located in package or on chip (data locality)

High wafer costs
Higher I/O count

- ▶ **Chiplets:** Use N node sparingly, keep some portion in N-1 node (e.g., I/O blocks)

Better PDN required

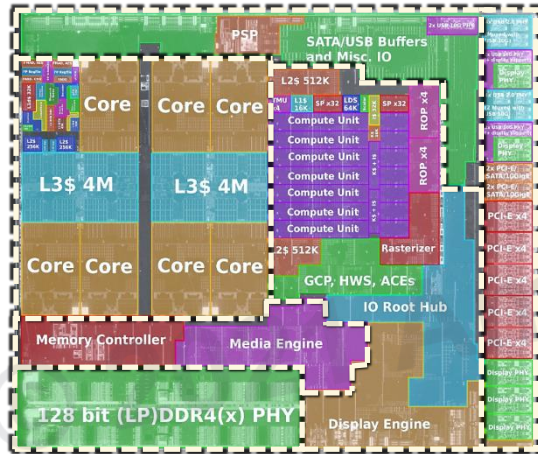
- ▶ Ultra low ESR caps, IPDs, VRMs (Voltage Regulator Modules)

Increasing dissipated power

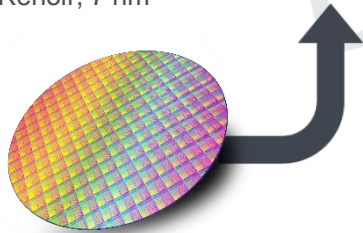
- ▶ Improve thermal power dissipation solution for the package

Power

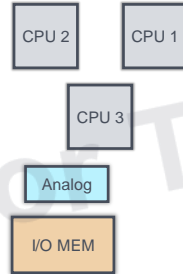
What are Chiplets?



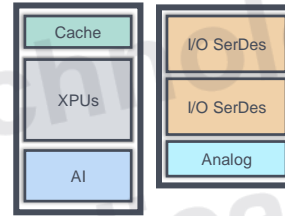
*AMD Renoir, 7 nm



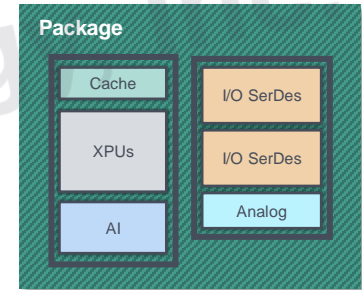
Functional Blocks



Chipllets

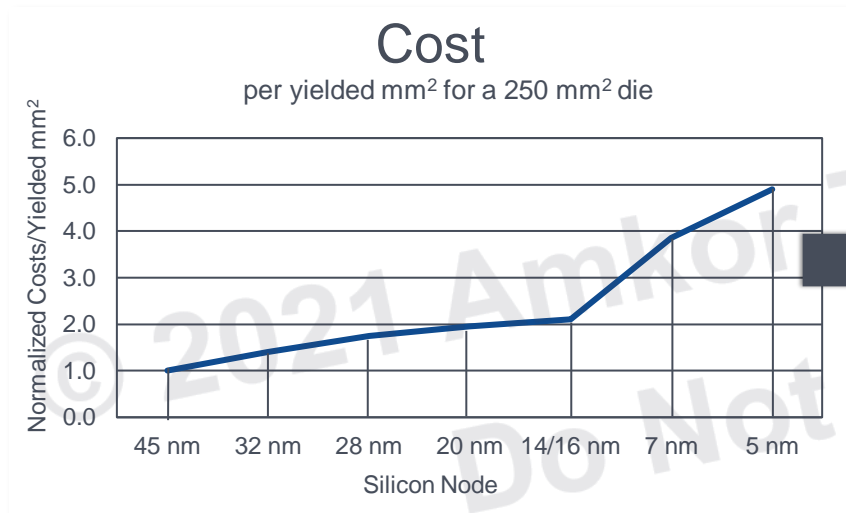


Product

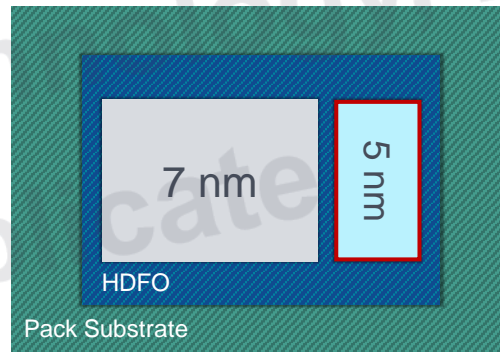


- ▶ Functional blocks are combined and partitioned into chiplets
- ▶ Chiplets are combined in the IC package to create the final product

Why Chiplets?



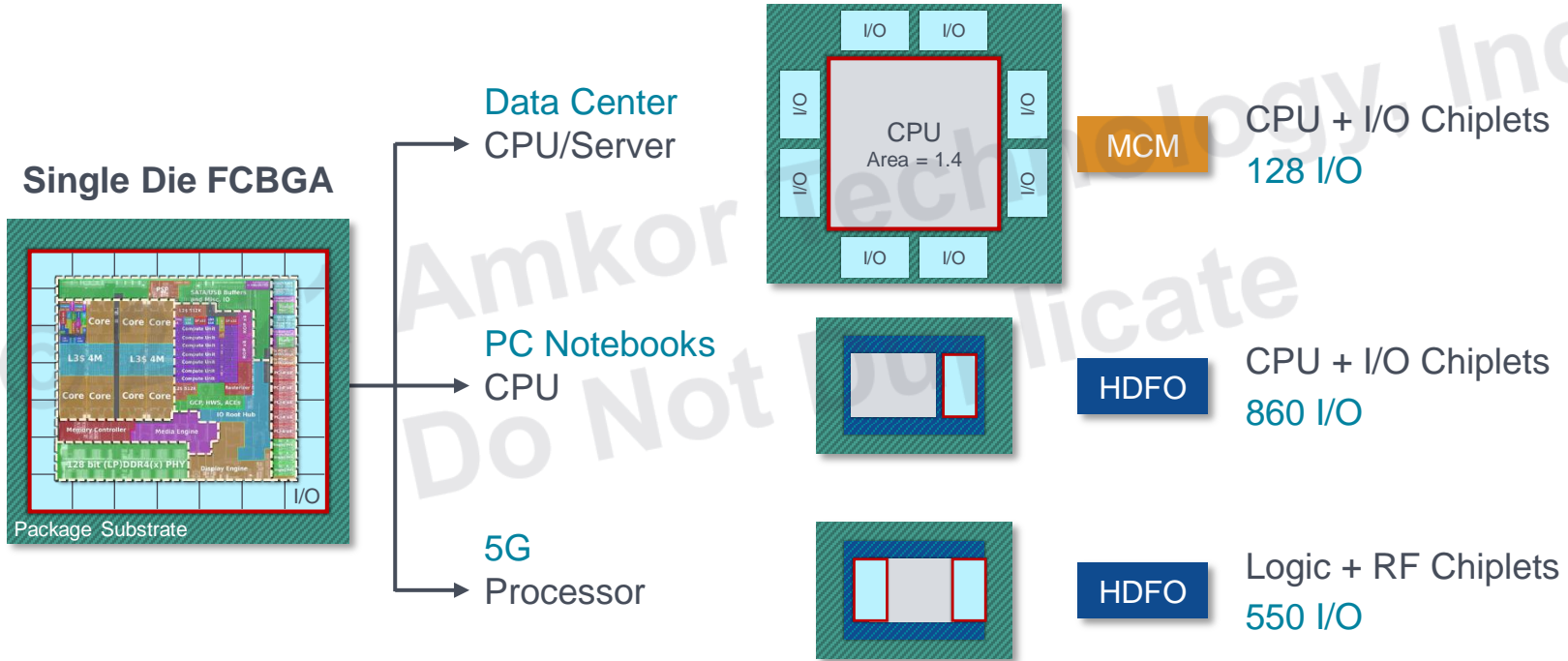
Performance



- ▶ Lower the total silicon cost
- ▶ Use latest Si node sparingly

- ▶ IC package-level integration enables same or greater performance
- ▶ Lower total product cost than SOC

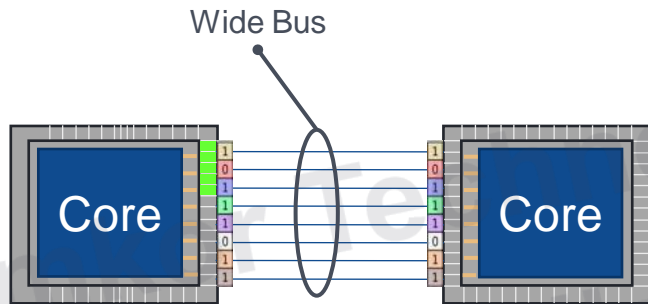
From SOC to Chiplets → Different Paths



Die-to-Die Interface: Package Differentiation

▶ Parallel interfaces

- ▶ More physical wires
- ▶ **Lower latency**
- ▶ Lower power

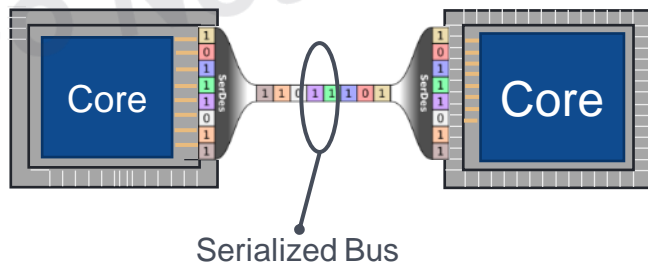


▶ Module based

- ▶ One physical wire/bit
- ▶ Each I/O driver is small
- ▶ High density routing
 - » HDFO
 - » 2.5D TSV

▶ Serial interfaces

- ▶ Fewer physical wires
- ▶ Higher latency
- ▶ Higher power



▶ MCM

- ▶ Many bits per wire pair
- ▶ Large I/O driver area

Chiplets and Heterogeneous Integration

Wafer Costs

Design Costs

Power Increases

IP Reuse

TTM

Better Power Dissip.

Better PDN

Deep Learning/AI Training

- ▶ Memory BW
- ▶ Lower power

NW Switch/Router

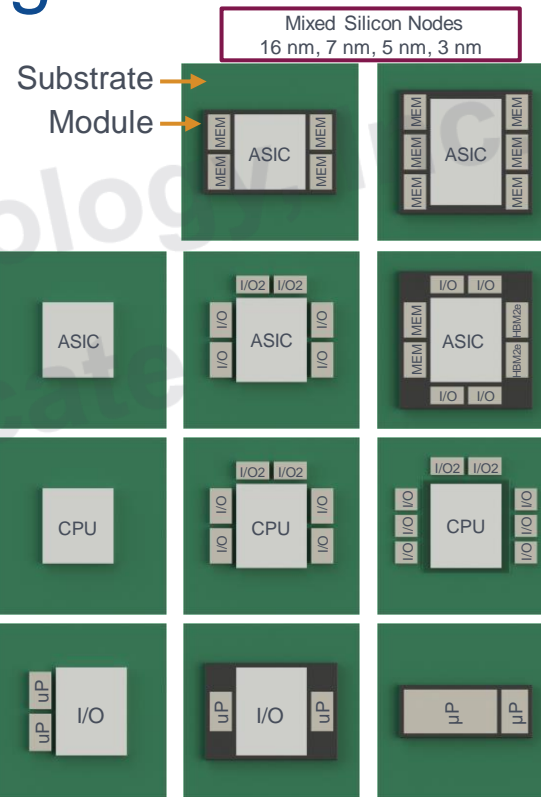
- ▶ Increase I/O count
- ▶ More gates

CPU, Server

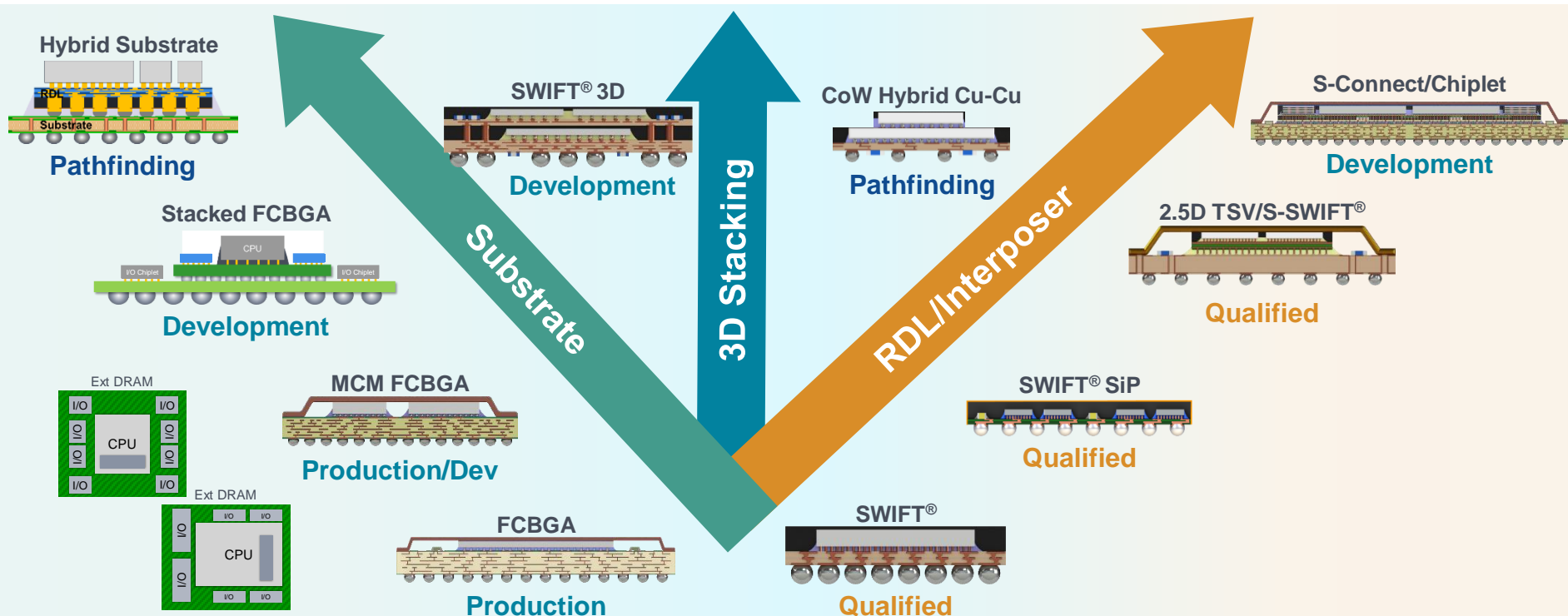
- ▶ Address more DRAM
- ▶ Client PC

PC CPU/GPU

- ▶ Lower cost



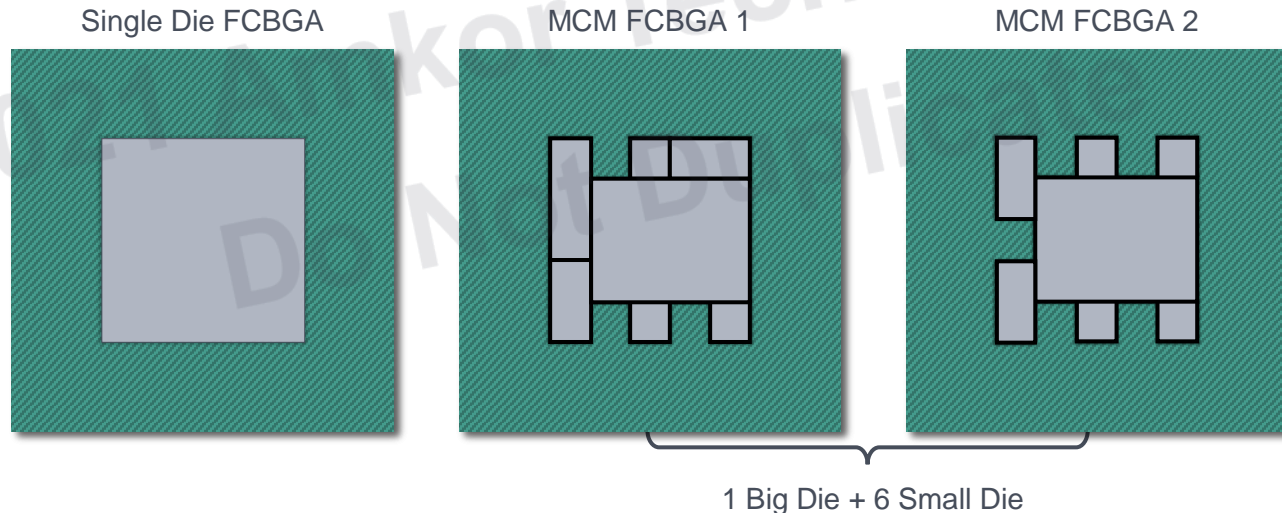
Chiplet Integration Path



High-Density MCM

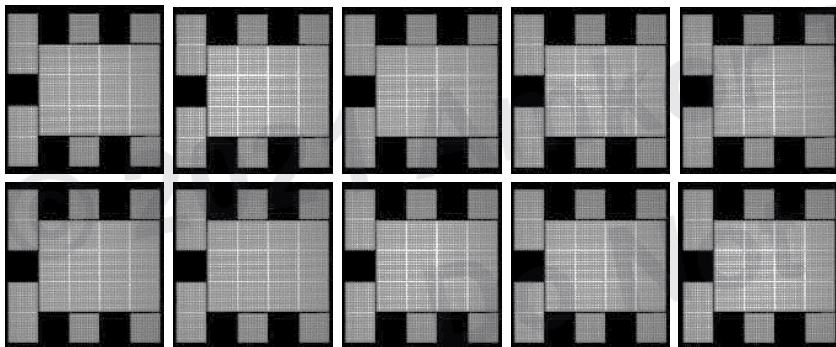
Test Vehicle

- ▶ In this device design a 32 x 32 mm die size was used with full array bumps at 165 μm pitch
- ▶ Same substrate was used for both single die & MCM study. Layout detailed below
- ▶ **70 μm die-die spacing**

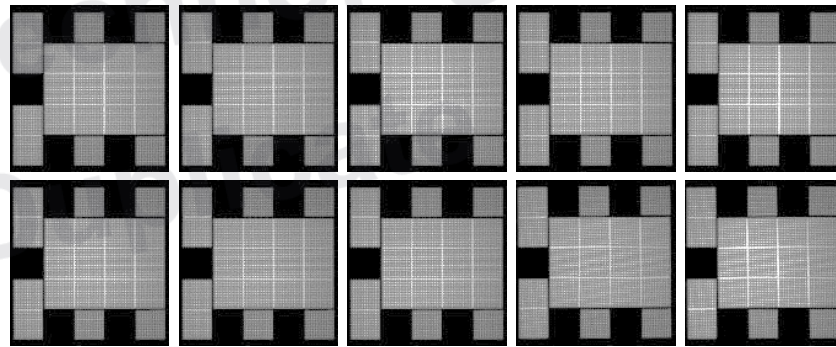


Development Results Summary: Reliability

- ▶ TCB 1,000x result
 - ▷ Found no UF abnormality



Leg 1: Individual side dispensing



Leg 2: One side dispensing

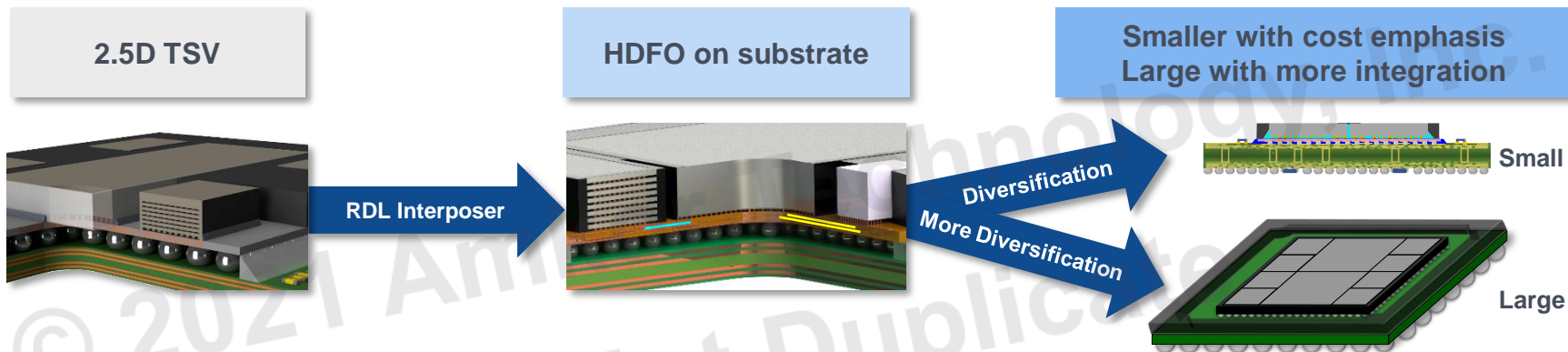


High-Density MCM

- ▶ Engineering feasibility completed
- ▶ UF dispense and cure demonstrated: Void-free
- ▶ Reliability (TCB only) demonstrated: No abnormality on both individual and single side dispensing
- ▶ Ready for customer prototyping

High-Density Fan-Out (HDFO) (S-SWIFT[®])

High-Density Fan-Out Evolution



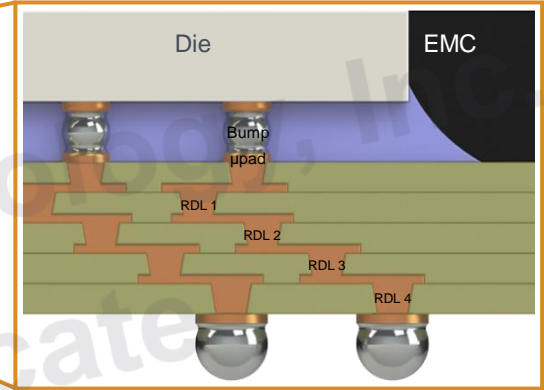
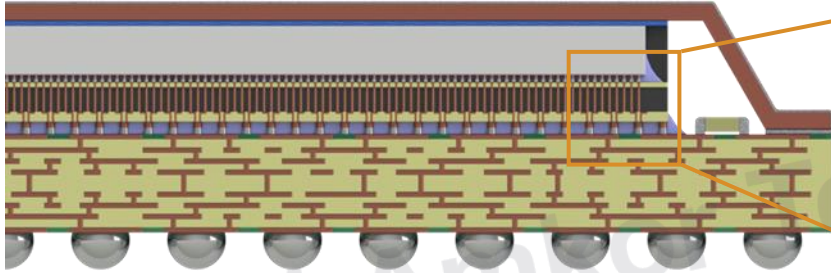
- ▶ Mostly logic + HBM2/2E

- ▶ Logic + HBM2/2E/3
- ▶ I/O die chiplets

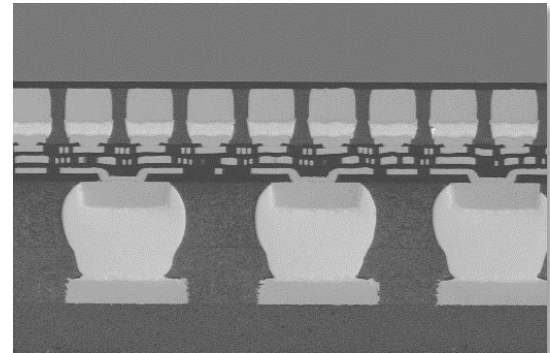
- ▶ **Cost emphasis**
 - ▷ Lower layer count
 - ▷ Die first and die last

- ▶ **Module size → 3x reticle area**
 - ▷ Better PDN solutions

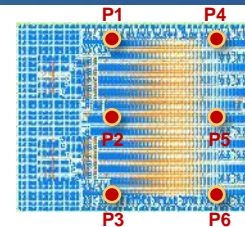
Substrate SWIFT® (S-SWIFT®)



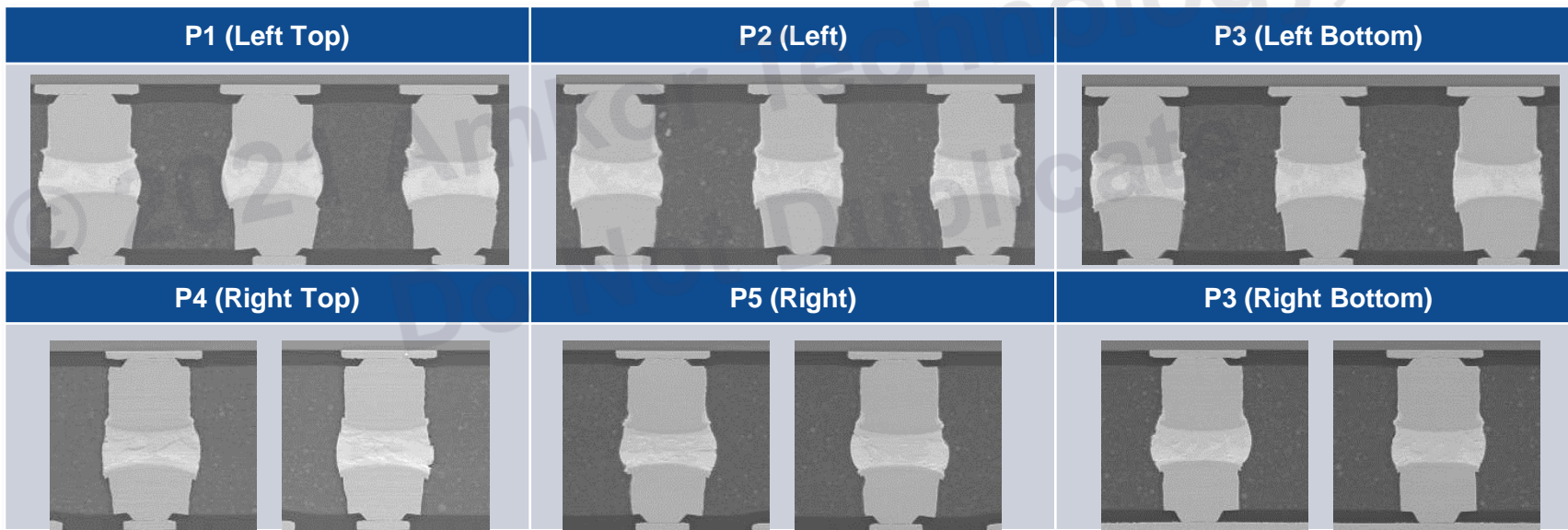
- ▶ Multilayer copper and organic dielectric RDL
- ▶ 2 μm line/space capability, 2-6 layers
- ▶ Excellent electrical properties
- ▶ Flexible solution
 - ▷ Fine pitch support for L1 down to 40 μm pitch
 - ▷ Plated Cu pillar or LF solder for L2 bumps



Cross Section Analysis – TCGG 1000x

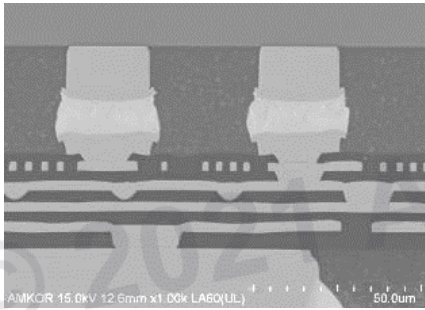


- ▶ HBM μ bump joint analysis
 - ▷ No abnormality was observed



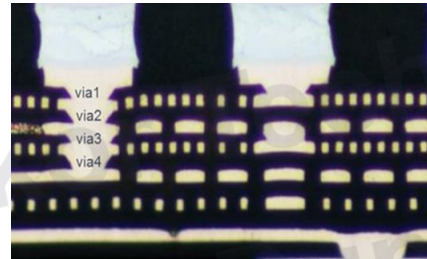
HDFO Status

2 μ m L/S, 4 Layer



- ▶ ~99% RDL yield
- ▶ Stacked vias with minimized dimple
- ▶ Reliable screen through AOI and in-line test
- ▶ Internal qualification completed for 4L 2/2

2 μ m L/S, 6 Layer



6L RDL for routing

- ▶ 6L development ongoing 2021
- ▶ Product qual 2022

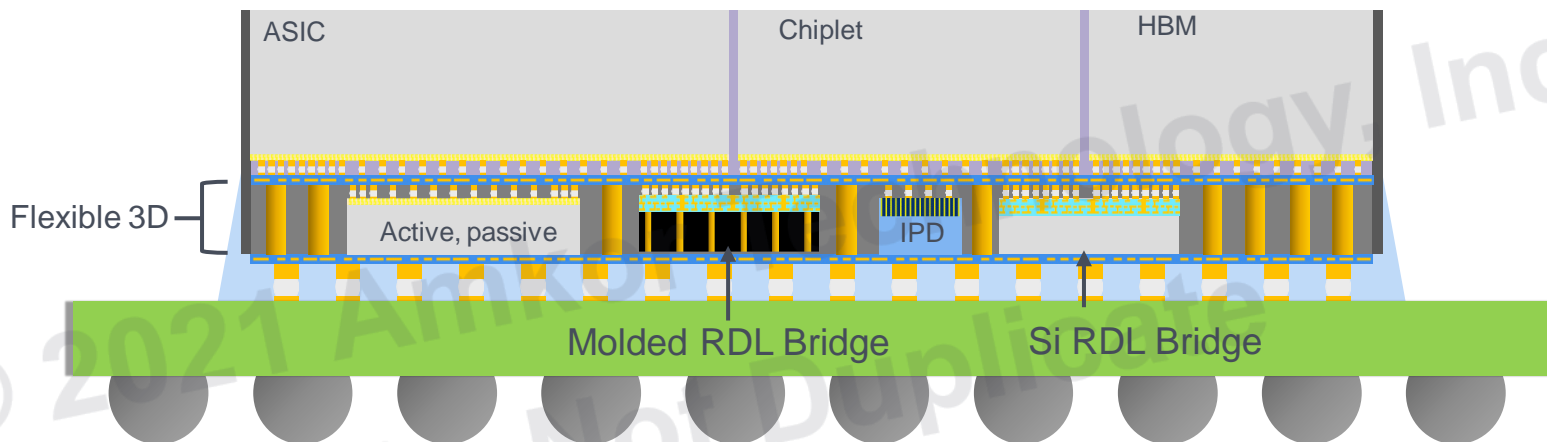
Larger Area, 3x Reticle



- ▶ Development ongoing

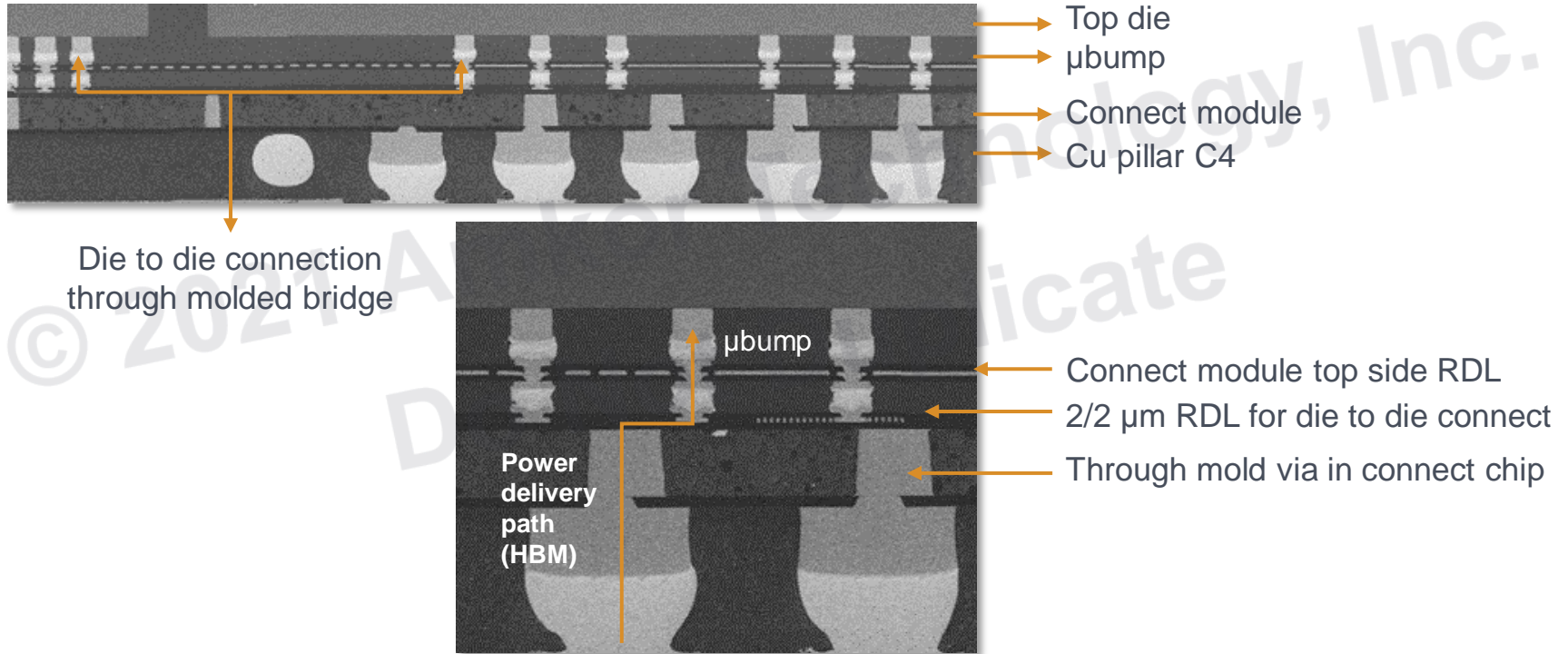
S-Connect (IPD and/or Bridge)

S-Connect



- ▶ Extended technology of SWIFT® and S-SWIFT®
- ▶ Bridge technology with embedded silicon connect dice for inter-chip connection
- ▶ IPD embedment for better power and signal integrity

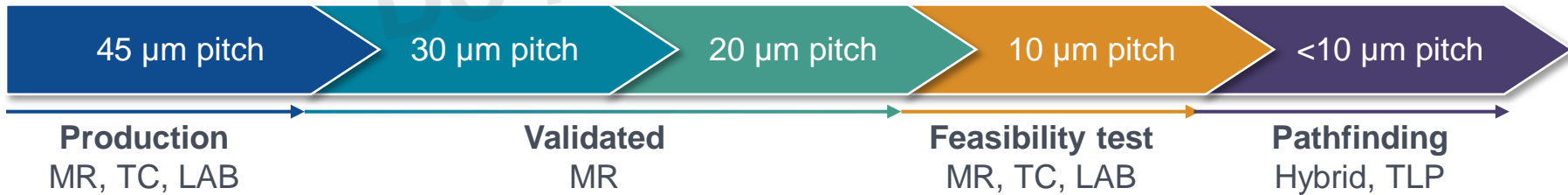
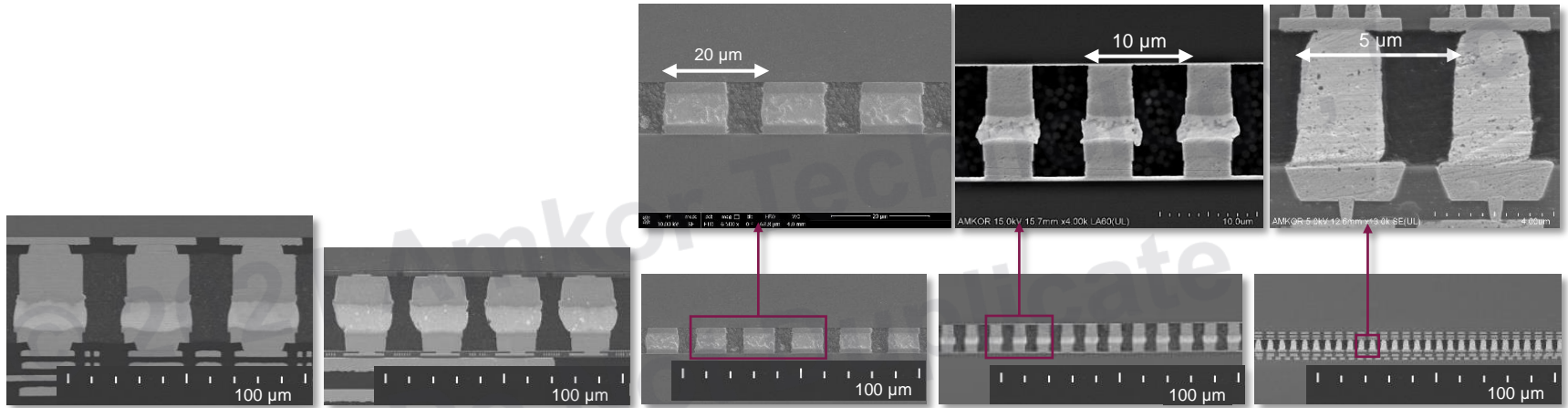
S-Connect with Molded Bridge





3D Stacking

Ultra Fine Pitch Bump Interconnection



Cu-Cu Hybrid Bonding

- ▶ 18 μm pitch CuP LF bump demonstrated for CoW application
- ▶ 10 μm pitch CuP LF bump demonstrated with Laser Assisted Bonding (LAB)
- ▶ Cu-Cu hybrid pathfinding ongoing
 - ▶ Amkor would like to co-develop with an alpha customer



Thank You

<https://amkor.com/tsv>

<https://amkor.com/fcbga>

<https://amkor.com/swift>

amkor.com



Thank you sponsors!

ADVANTEST[®]



SYNOPSYS[®]



Global Companies Rate Advantest THE BEST ATE Company 2021



Advantest receives highest ratings from customers in annual VLSresearch Customer Satisfaction Survey for 2 consecutive years.

Global customers name Advantest THE BEST supplier of test equipment in 2020 and 2021, with highest ratings in categories of:

**Technical Leadership – Partnership – Trust
– Recommended Supplier – Field Service**

“Year-after-year the company has delivered on its promise of technological excellence and it remains clear that Advantest keeps their customers’ successes central to their strategy. Congratulations on celebrating 33 years of recognition for outstanding customer satisfaction.”

— Risto Puhakka, President VLSresearch

Amkor's Differentiators



Technology

Advanced Packaging Leadership
Engineering Services
Broad Portfolio



Quality

QualityFIRST Culture
Execution
Automation



Service

Design & Test Through Drop Ship
Manufacturing Footprint
Local Sales & Support

SYNOPSYS®

Silicon to Software™

COPYRIGHT NOTICE

This presentation in this publication was presented at the **Road to Chiplets: Architecture Workshop** (July 13 & 14, 2021). The content reflects the opinion of the author(s) and their respective companies. The inclusion of presentations in this publication does not constitute an endorsement by MEPTEC or the sponsors.

There is no copyright protection claimed by this publication. However, each presentation is the work of the authors and their respective companies and may contain copyrighted material. As such, it is strongly encouraged that any use reflect proper acknowledgement to the appropriate source. Any questions regarding the use of any materials presented should be directed to the author(s) or their companies.

www.meptec.org